

Status of the CALICE ECAL

CALICE collaboration

http://polywww.in2p3.fr/flc/calice.html

- Introduction
- The proposed calorimeter
- The ECAL prototype
- R&D for next generation
- Schedule

LCWS04, 22/04/04

- Silicon wafer
- PCB
- VFE Chip
- Gluing
- · DAQ
- First measurements
- New chip
- Thermal studies
- AC coupling (silicon)
- PCB

It is not R&D in the back yard !!

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LCWS04



Start from physics

See what design/technique could fit

List the R&D to do to validate the choice

Study potential performance with simul.

Optimise EFLOW performances lead to optimize close showers separability so, like digital camera

→ number of pixel !!!!

LCWS04, 22/04/04











Silicon Wafers for the prototype 4" High resistive wafer : 5 KΩcm Si Wafer : Thickness : 525 microns + 3 % 6×6 pads of detection Tile side : 62.0 + 0.0 $(10 \times 10 \text{ mm}^2)$ - 0.1 mm 62 mm In Silicone ~80 e-h pairs / micron \Rightarrow 42000 e⁻ /MiP Capacitance : ~21 pF Leakage current : 5 – 15 nA Full depletion bias : ~150 V 62 mm Nominal operating bias : 200 V

One wafer is a Matrix of 6 x 6 pixel of 1 cm^2 . Important point : manufacturing must be as simple as possible to be near of what could be the real production for full scale detector in order to :

- Keep lower price (a minimum of step during processing)
- Low rate of rejected processed wafer
- good reliability and large robustness

LCWS04, 22/04/04

Guard ring



Silicon Wafers for the prototype

Number of active Wafer needed for the physic prototype : 270.

150 produce by Institute of Nuclear Physics - Moscow State University (M. Merkin, A. Savin , A. Voronin)

- First test production : February 2003
- Today : ~130 matrices

150 produce by Institute of Physics, Academy of Sciences of the Czech Republic – Prague (V .Vrba)

- First test production : March 2004 (6 good wafers)
- Full prod for end of May.



Silicon Wafers for the prototype

Institute of Nuclear Physics Moscow State University



Institute of Physics, Academy of Sciences of the Czech Republic



One process gives results which fit the spec.

LCW504, 22/04/04





Mounting/Gluing the wafers

A automatic device is use to deposit the conductive glue : EPO-TEK® EE129-4



X-Y-Z table $(400 \times 400 \times 150 \text{ mm}^3)$ with glue dispensing tool (conductive glue)

Gluing and placement (\pm 0.1 mm) of 270 wafers with 6×6 pads About 10 000 points of glue.

Mounting/gluing the wafers

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Cosmic test bench





The ECAL prototype schedule

March – November 2004 Assembling and testing on a cosmic test bench Intercalibration of the 10K channels and overall debug !

~ December 2004 at DESY (Low energy electrons E<6 GeV) First test beam

2005-2006 at FNAL/IHEP/SLAC ? (electrons/pions/protons up to ~80 GeV) test beam with HCAL ...

R&D in ECAL-CALICE



ADC-DAQ board with low consumption, small dimension, >100 channels/board

